

Features

- Trench Power LV MOSFET Technology
- High Density Cell Design For Low $R_{DS(on)}$
- Moisture Sensitivity Level 3
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

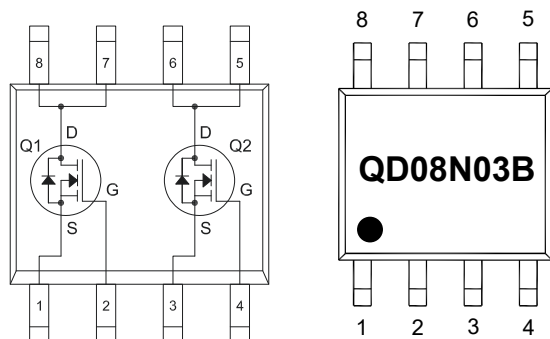
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 80°C/W Junction to Ambient (Note2)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	I_D	$T_A=25^\circ\text{C}$	8
		$T_A=100^\circ\text{C}$	5.1
Pulsed Drain Current (Note 3)	I_{DM}	32	A
Total Power Dissipation (Note 4)	P_D	1.6	W
Single Pulsed Avalanche Energy (Note 5)	E_{AS}	16	mJ

Note:

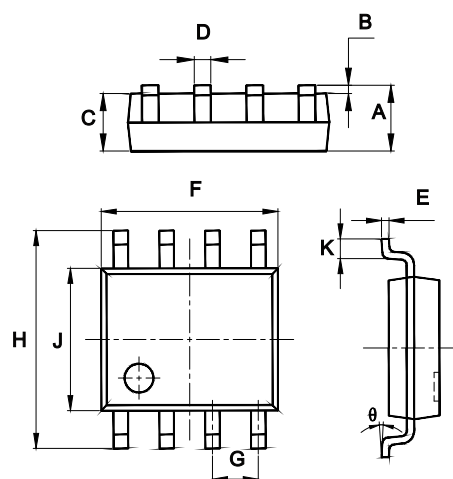
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-ambient thermal resistance.
5. $T_J=25^\circ\text{C}$, $V_{DD}=30\text{V}$, $V_{GS}=10\text{V}$, $L=0.5\text{mH}$.

Internal Structure and Marking Code



Dual N-CHANNEL MOSFET

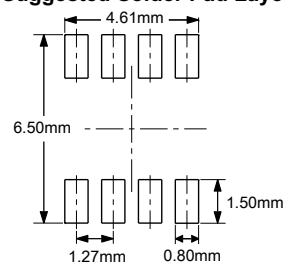
SOP-8



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.053	0.069	1.35	1.75	
B	0.004	0.010	0.10	0.25	
C	0.053	0.061	1.35	1.55	
D	0.013	0.020	0.33	0.51	
E	0.007	0.010	0.17	0.25	
F	0.185	0.200	4.70	5.10	
G	0.050		1.270		TYP.
H	0.228	0.244	5.80	6.20	
J	0.150	0.157	3.80	4.00	
K	0.016	0.035	0.40	0.90	
θ	0°	8°	0°	8°	

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.6	0.9	1.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=8A$		19	25	m Ω
		$V_{GS}=4.5V, I_D=6A$		21	30	
		$V_{GS}=2.5V, I_D=3A$		26	40	
Gate Resistance	R_g	f=1 MHz, Open drain		1.8		Ω
Drain-Source Diode Characteristics						
Diode Forward Current	I_S				8.0	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=8A$			1.2	V
Reverse Recovery Time	t_{rr}	$I_F=5.6A, di/dt=100A/\mu s$		10		nS
Reverse Recovery Charge	Q_{rr}			3.7		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, f=1MHz$		580		pF
Output Capacitance	C_{oss}			60		
Reverse Transfer Capacitance	C_{rss}			50		
Total Gate Charge	Q_g	$V_{DS}=15V, V_{GS}=10V, I_D=5.6A$		16.3		nC
Gate-Source Charge	Q_{gs}			2.2		
Gate-Drain Charge	Q_{gd}			2.1		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, V_{GS}=10V, I_D=5.6A, R_G=3\Omega$		5.5		ns
Turn-on Rise Time	t_r			28.3		
Turn-off Delay Time	$t_{d(off)}$			24.8		
Turn-off Fall Time	t_f			13.7		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

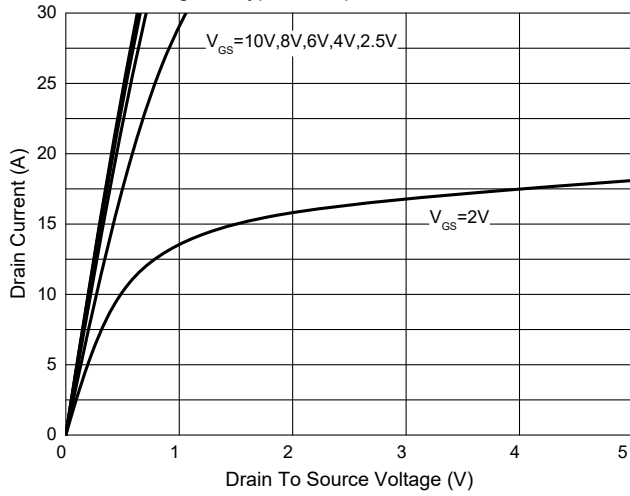


Fig. 2 - Transfer Characteristics

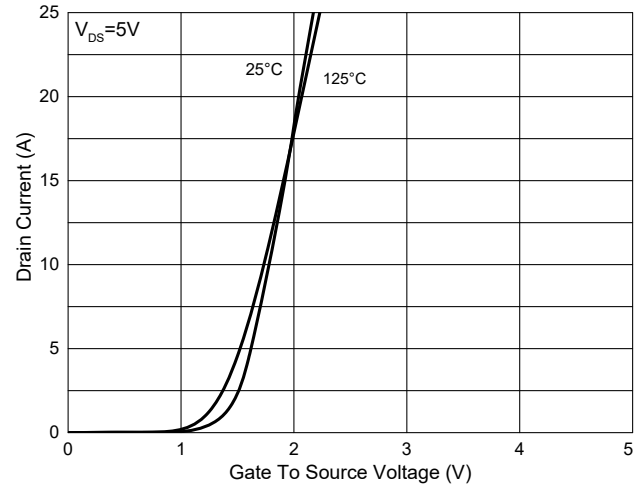


Fig. 3 - $R_{DS(ON)} - V_{GS}$

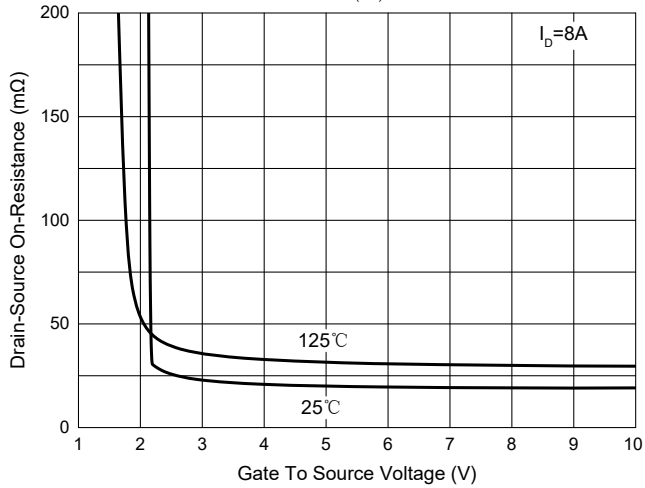


Fig. 4 - $R_{DS(ON)} - I_D$

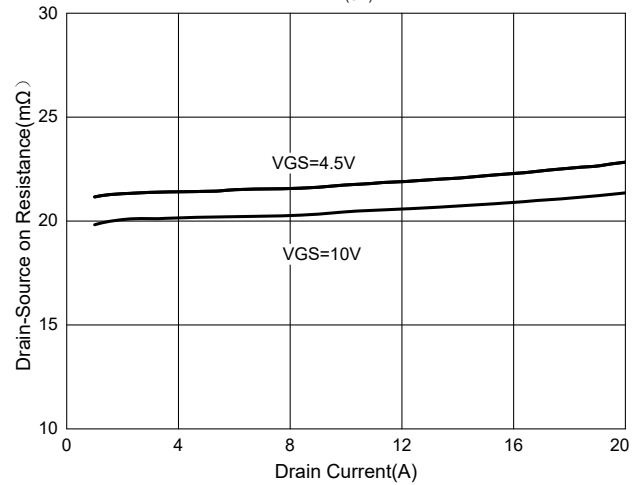


Fig. 5 - Capacitance Characteristics

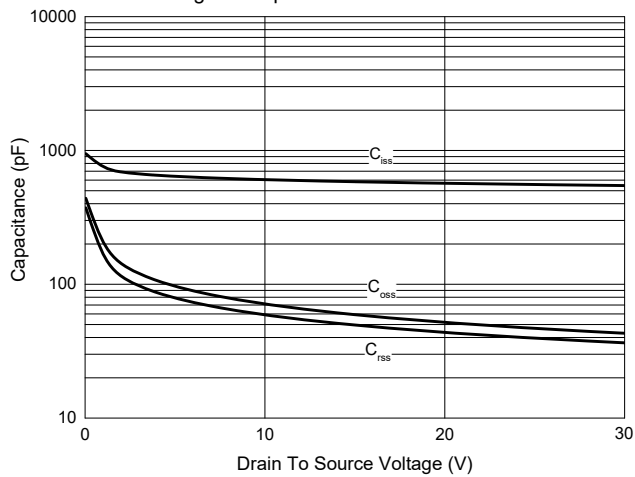
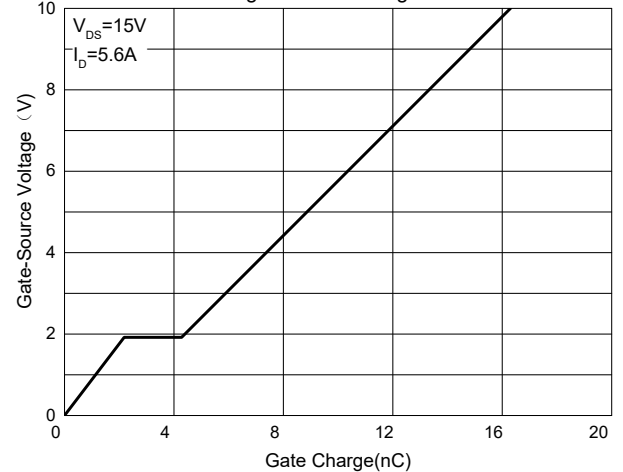


Fig. 6 - Gate Charge



Curve Characteristics

Fig. 7 - Normalized Threshold Voltage

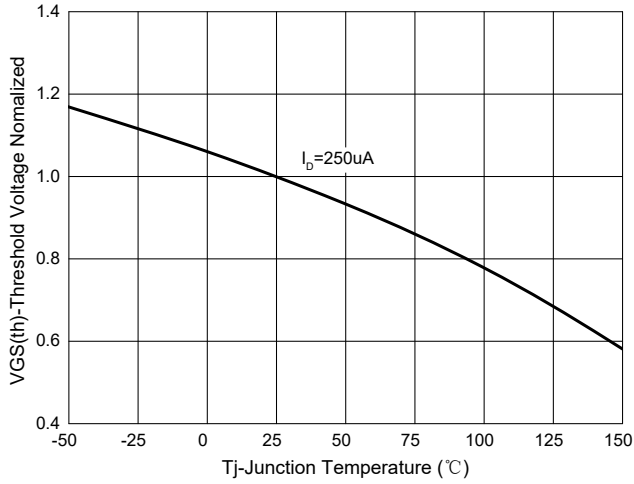


Fig.8-Normalized On Resistance Characteristics

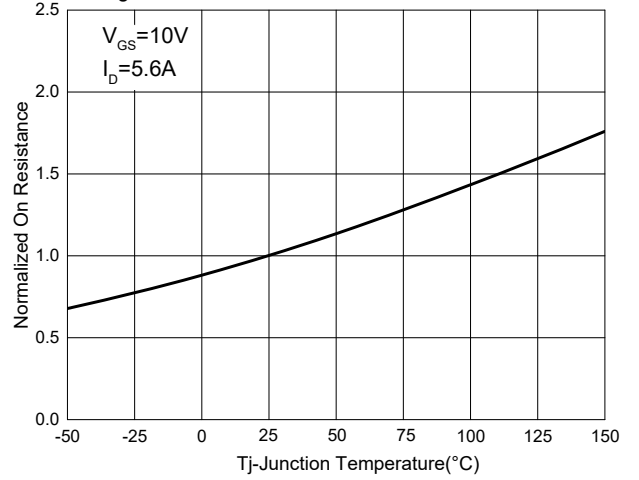


Fig.9 - I_s—V_{SD}

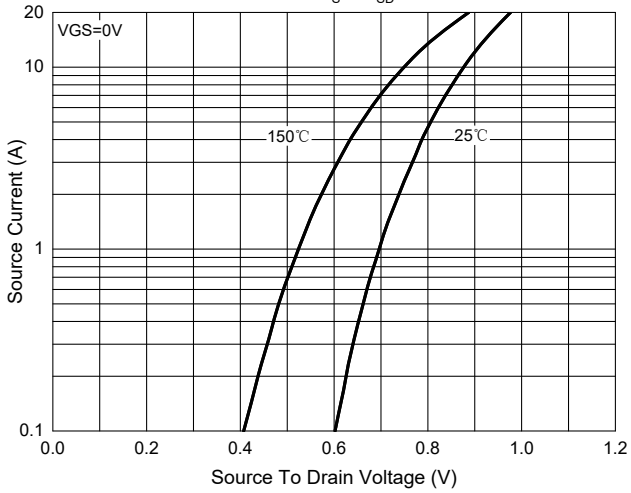


Fig. 10 - Drain Current

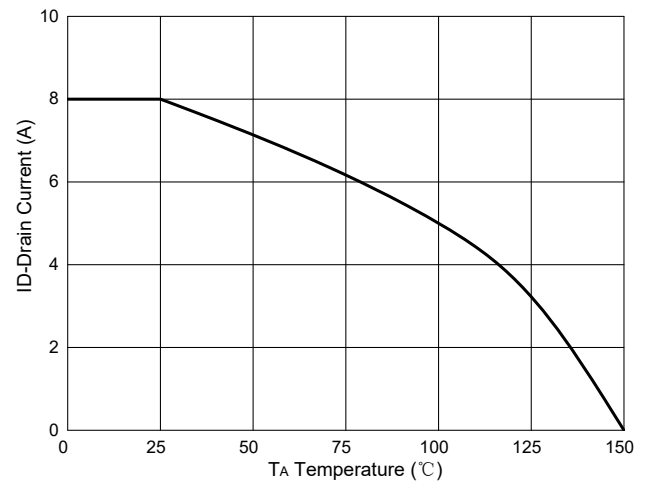
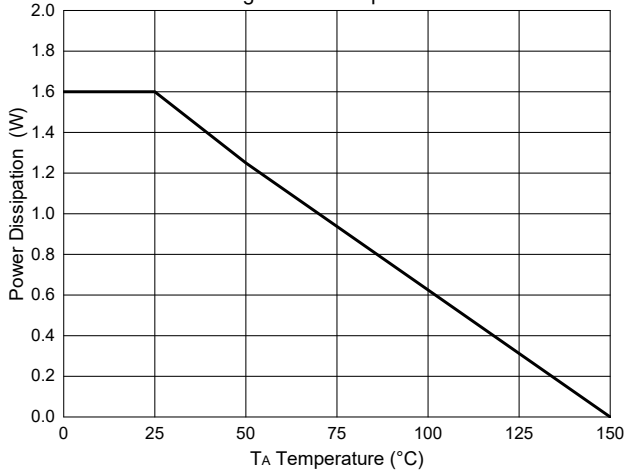


Fig.11-PD Dissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

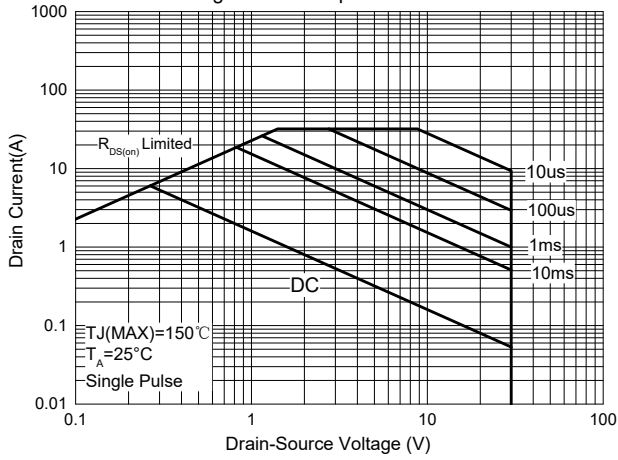
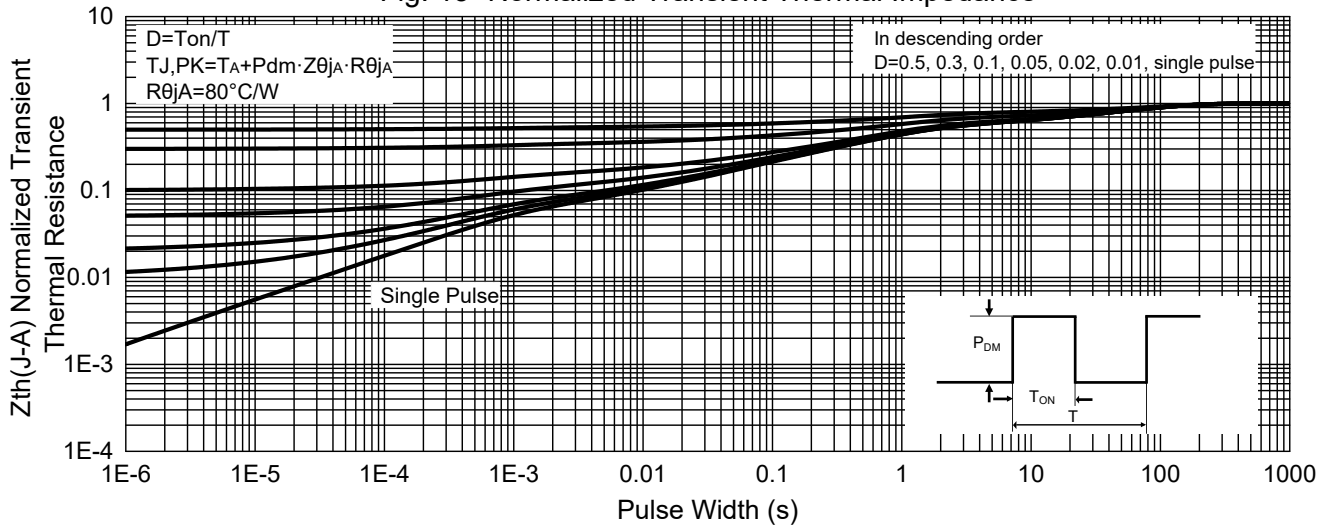


Fig. 13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 4Kpcs/Reel

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